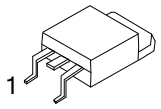
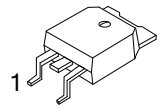
9N65-TC2 **Preliminary** ***Power MOSFET***

9A, 650V N-CHANNEL POWER MOSFET



TO-252



TO-252D

■ DESCRIPTION

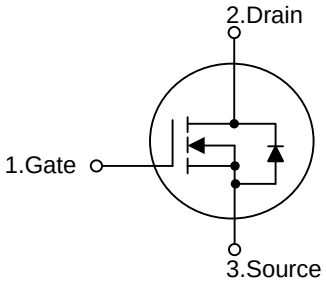
The UTC **9N65-TC2** is an N-channel mode power MOSFET using UTC's advanced technology to provide costumers with planar stripe and DMOS technology. This technology is specialized in allowing a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

The UTC **9N65-TC2** is universally applied in active power factor correction and high efficient switched mode power supplies.

■ FEATURES

* $R_{DS(ON)} \leq 1.3\ \Omega$ @ V_{GS}=10V, I_D=4.5A
* High switching speed
* Improved dv/dt capability

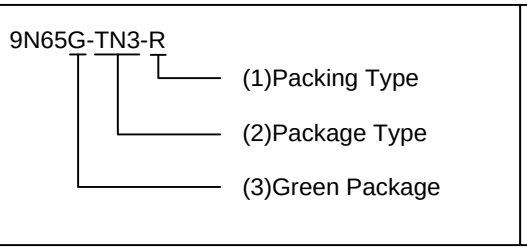
■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
9N65L-TN3-R	9N65G-TN3-R	TO-252	G	D	S	Tape Reel
9N65L-TND-R	9N65G-TND-R	TO-252D	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

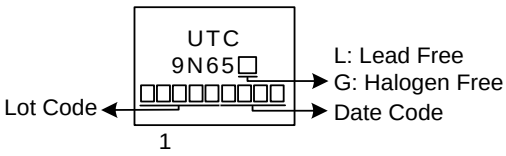


(1) R: Tape Reel

(2) TN3: TO-252, TND: TO-252D

(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain to Source Voltage		V_{DSS}	650	V
Gate to Source Voltage		V_{GSS}	±30	V
Continuous Drain Current	Continuous	I_D	9	A
	Pulsed (Note 2)	I_{DM}	18	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	240	mJ
Peak Diode Recovery dv/dt (Note 3)		dv/dt	4.5	V/ns
Power Dissipation		P_D	55	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating : Pulse width limited by maximum junction temperature.
3. L = 30mH, I_{AS} = 4.0A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C
4. I_{SD} ≤9.0A, di/dt ≤200A/μs, V_{DD} ≤BV_{DSS}, Starting T_J=25°C.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	110	°C/W
Junction to Case	θ_{JC}	2.27 (Note)	°C/W

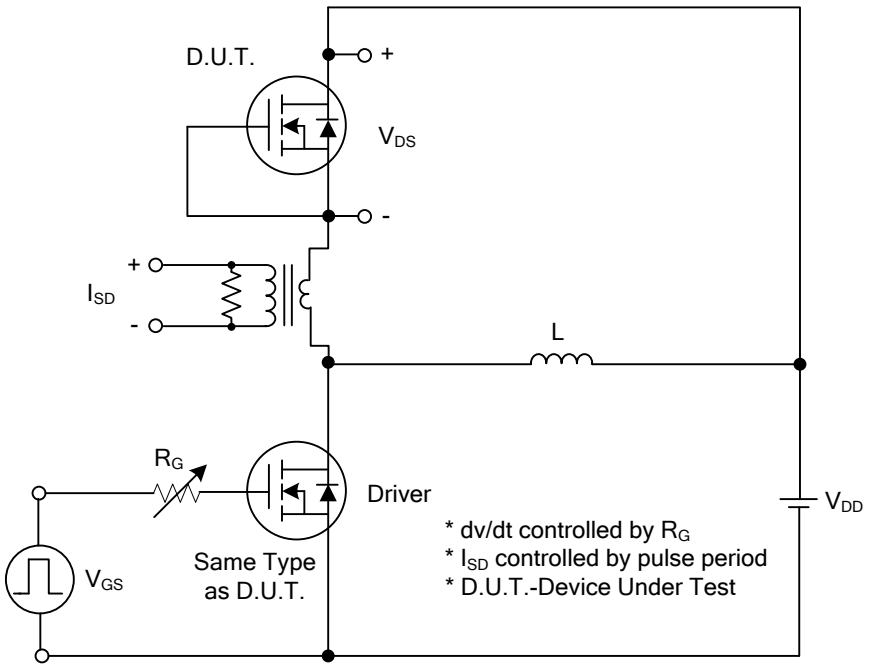
Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

■ ELECTRICAL CHARACTERISTICS (T_J =25°C, unless otherwise specified)

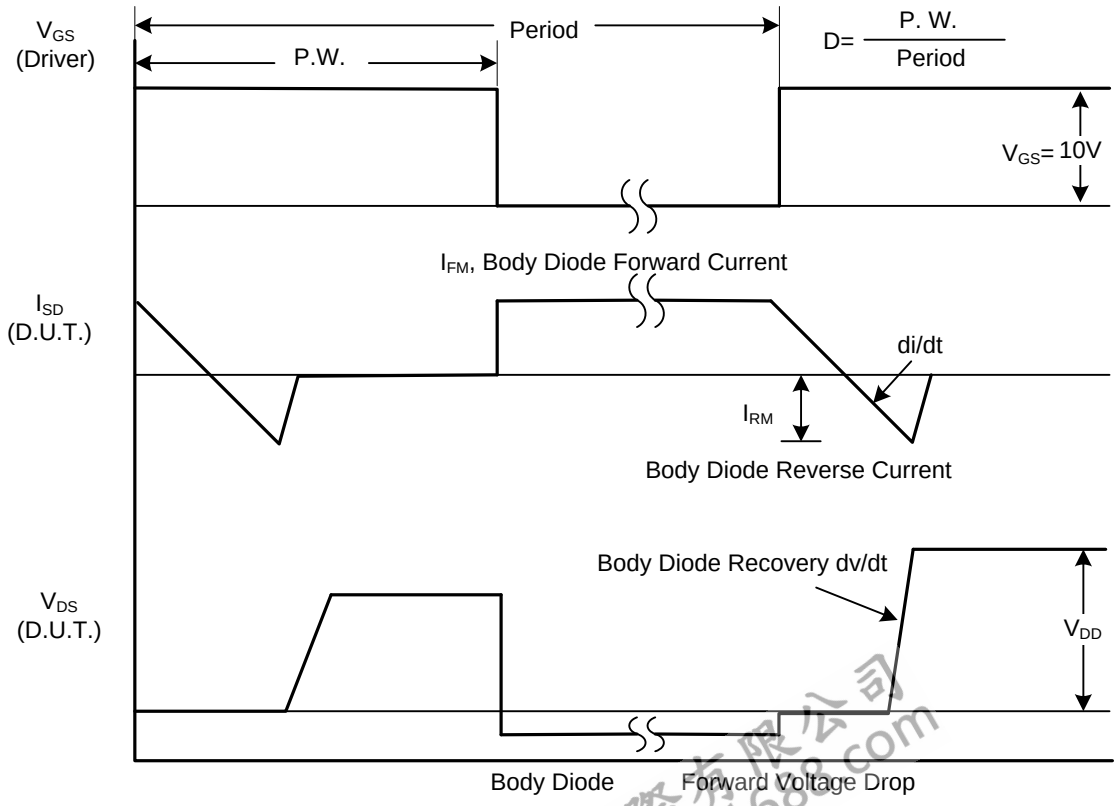
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS}=0V, I_D=250μA	650			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=650V, V_{GS}=0V			10	μA
Gate- Source Leakage Current	Forward	I_{GSS}	V_{GS}=+30V, V_{DS}=0V			+100	nA
	Reverse		V_{GS}=-30V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	2.0		4.0	V
Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=4.5A			1.3	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C_{ISS}	V_{DS}=25V, V_{GS}=0V, f=1MHz		1150		pF
Output Capacitance		C_{OSS}			110		pF
Reverse Transfer Capacitance		C_{RSS}			4.8		pF
DYNAMIC CHARACTERISTICS							
Total Gate Charge		Q_G	V_{DS}=520V, V_{GS}=10V, I_D=9A I_G=1mA (Note 1, 2)		25		nC
Gate-Source Charge		Q_{GS}			6.5		nC
Gate-Drain Charge		Q_{GD}			4.2		nC
Turn-on Delay Time (Note 1)		$t_{D(ON)}$	V_{DS}=100V, V_{GS}=10V, I_D=9A, R_G=25Ω (Note 1, 2)		13.5		ns
Rise Time		t_R			18		ns
Turn-off Delay Time		$t_{D(OFF)}$			78		ns
Fall-Time		t_F			36		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Continuous Drain-Source Diode Forward Current		I_S				9	A
Maximum Pulsed Drain-Source Diode Forward Current		I_{SM}				18	A
Drain-Source Diode Forward Voltage (Note 1)		V_{SD}	I_S =9A, V_{GS}=0V			1.4	V
Body Diode Reverse Recovery Time (Note 1)		t_{rr}	I_S =9A, V_{GS}=0V, dI_F/dt=100A/μs		470		nS
Body Diode Reverse Recovery Charge		Q_{rr}			9.5		μC

Notes: 1. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

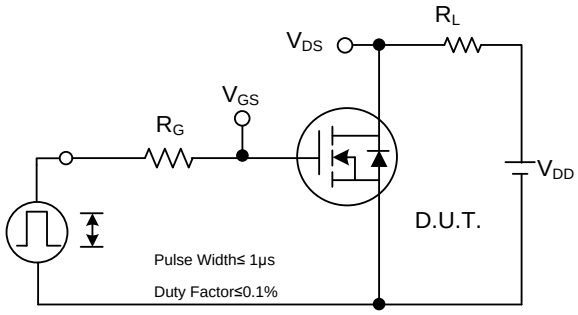


Peak Diode Recovery dv/dt Test Circuit

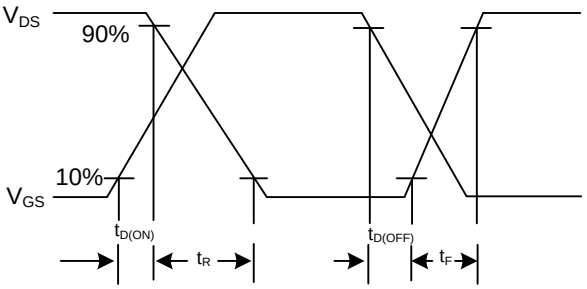


Peak Diode Recovery dv/dt Waveforms

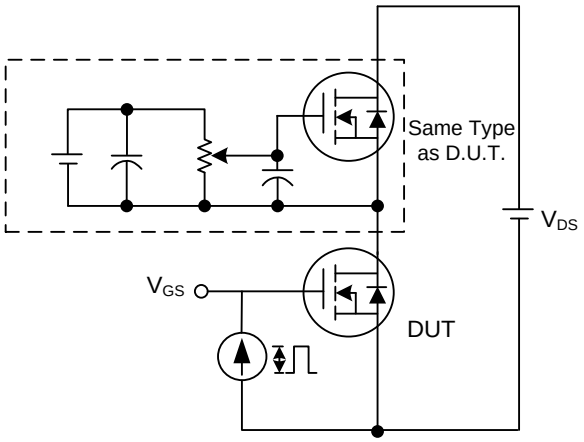
■ TEST CIRCUITS AND WAVEFORMS



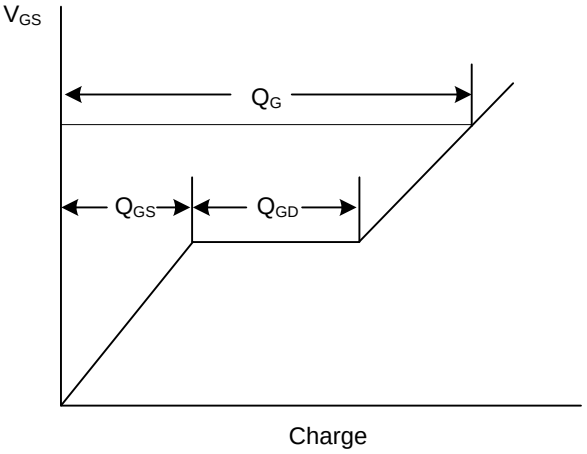
Switching Test Circuit



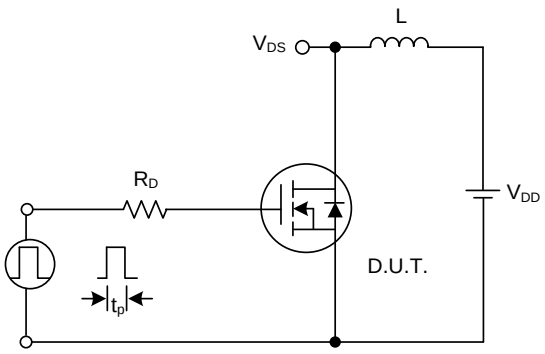
Switching Waveforms



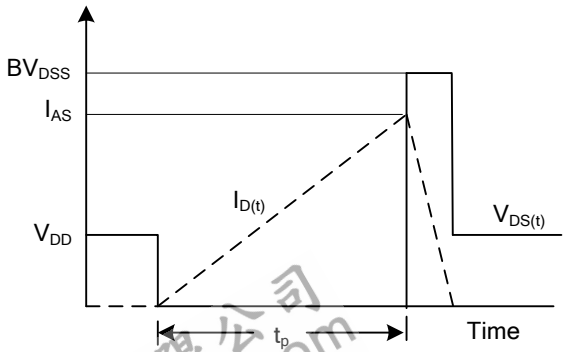
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms